

What is claimed is:

1. A method of manufacturing a semiconductor device,
comprising:

forming terminal portions convexly protruding on a surface
5 of first conductive foil by etching the first conductive foil
except portions to become terminals;

superimposing a resin sheet on the first conductive foil
such that the terminal portions are embedded in the resin sheet;

constructing a laminated sheet by superimposing second
10 conductive foil on the resin sheet;

forming a conductive pattern by etching the second
conductive foil;

electrically connecting the conductive pattern and the
terminal portions;

15 electrically isolating the terminal portions from each
other;

firmly fixing a semiconductor element to the laminated
sheet and electrically connecting the semiconductor element and
the conductive pattern; and

20 forming sealing resin on a surface of the laminated sheet
such that the semiconductor element is covered by the sealing
resin.

2. The method according to claim 1, wherein the terminal
portions are electrically isolated from each other by etching
25 the first conductive foil from a back thereof.

3. The method according to claim 1, wherein the resin sheet
is made of soluble resin, and side surfaces of the terminal
portions are exposed by removing the resin sheet.

4. The method according to claim 1, wherein the semiconductor element is connected face-up, and an electrode of the semiconductor element and the conductive pattern are connected through a fine metallic wire.

5 5. The method according to claim 1, wherein the semiconductor element is mounted face-down, and an electrode of the semiconductor element and the conductive pattern are connected through a bump electrode.